

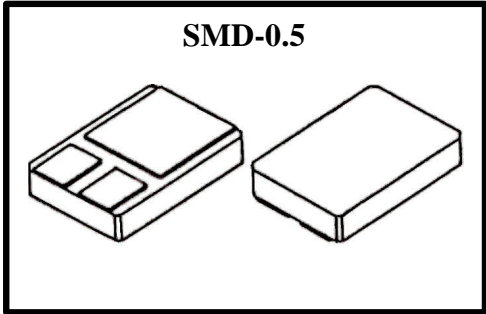
1N6845

**45 VOLTS, 40 AMP
 SCHOTTKY RECTIFIER
 CERAMIC SURFACE MOUNT**

DESIGNER'S DATA SHEET

FEATURES:

- Low Profile Ceramic SMD
- High Surge Rating
- Low Reverse Leakage Current
- Low Forward Voltage
- Seam Welded Package
- Low Capacitance
- Ultrasonic Aluminum Wire Bonds



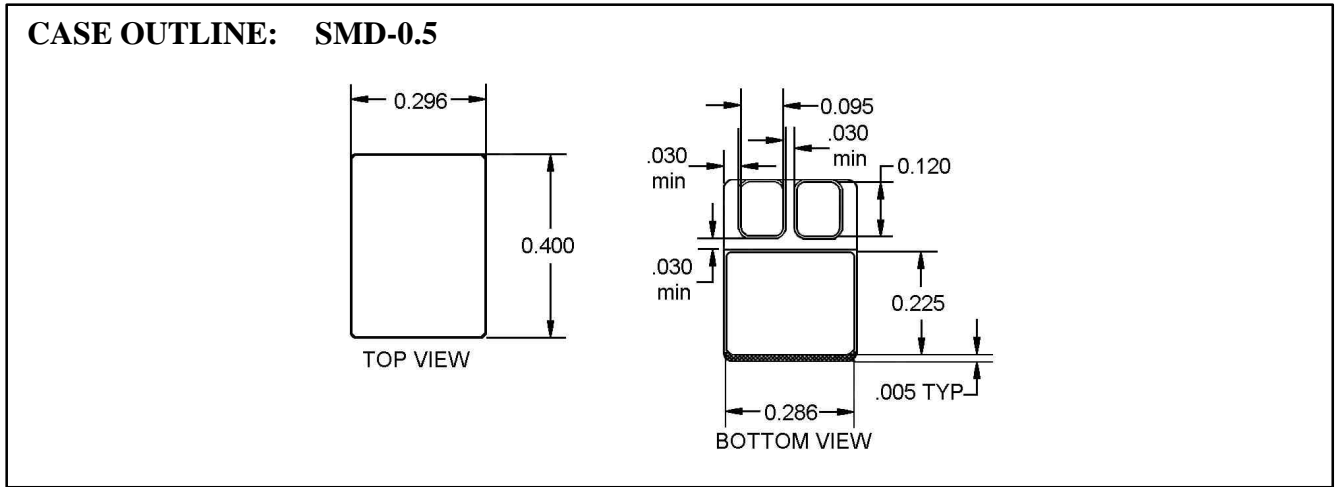
MAXIMUM RATINGS

| RATING | SYMBOL | VALUE | UNIT |
|-------------------------------------------------------------------------------------------------|-----------------------------------------|-------------|----------------|
| Peak Repetitive Reverse and DC Blocking Voltage 1N6845 | V_{RRM} V_{RWN} V_R | 45 | Volts |
| Average Rectified Forward Current (Resistive Load, 60Hz, Sine Wave, $T_A = 25^\circ C$) | I_o | 40 | Amps |
| Peak Surge Current 8.3 ms Pulse, $T_A = 25^\circ C$ | I_{FSM} | 400 | Amps |
| Operating & Storage Temperature | Top & Tstg | -55 to +150 | $^\circ C$ |
| Maximum Thermal Resistance Junction to Case, | $R_{\theta JC}$ | 2.0 | $^\circ C / W$ |

1/4/00

ELECTRICAL CHARACTERISTICS

| CHARACTERISTICS | SYMBOL | MAX. | UNIT |
|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------|-------------------------------------------|---------------|
| Instantaneous Forward Voltage Drop ($I_F = 10 \text{ Adc}$, $T_A = 25^\circ\text{C}$, 300 μs Pulse) ($I_F = 20 \text{ Adc}$, $T_A = 25^\circ\text{C}$, 300 μs Pulse) ($I_F = 40 \text{ Adc}$, $T_A = 25^\circ\text{C}$, 300 μs Pulse) | V_F | 0.65 0.72 0.86 | Vdc |
| Instantaneous Forward Voltage Drop ($I_F = 20 \text{ Adc}$, $T_A = 100^\circ\text{C}$, 300 μs Pulse) ($I_F = 20 \text{ Adc}$, $T_A = -55^\circ\text{C}$, 300 μs Pulse) | V_F | 0.65 0.78 | Vdc |
| Reverse Leakage Current (Rated V_R , $T_A = 25^\circ\text{C}$, 300 μs pulse minimum) | I_R | 100 | μA |
| Reverse Leakage Current (Rated V_R , $T_A = 100^\circ\text{C}$, 300 μs pulse minimum) | I_R | 10 | mA |
| Junction Capacitance ($V_R = 10\text{Vdc}$, $T_A = 25^\circ\text{C}$, $f = 1 \text{ MHz}$) | C_J | 800 | Pf |



TYPICAL OPERATING CURVES
 (TA=25°C Unless otherwise specified)

